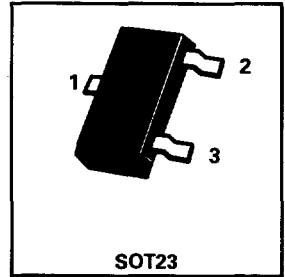
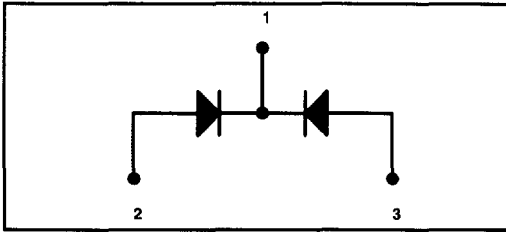


# SOT23 SILICON PLANAR LOW LEAKAGE COMMON CATHODE DIODE PAIR

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## FLLD258



PART MARKING DETAIL – D58

### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Repetitive Peak Reverse Voltage	$V_{RRM}$	100	V
Average Rectified Forward Current	$I_{F(AV)}$	250	mA
Non-Repetitive Peak Forward Current ( $t=1\mu s$ )	$I_{FSM}$	3.0	A
Power Dissipation at $T_{amb} = 25^{\circ}C$	$P_{tot}$	330	mW
Operating and Storage Temperature Range	$T_j: T_{stg}$	-55 to +150	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Reverse Current	$I_R$		3 5	nA $\mu A$	$V_{RRM}=50V$ $V_{RRM}=100V, T_{amb}=150^{\circ}C$
Reverse Recovery Time*	$t_{rr}$		400	ns	$I_F = I_R = 50 - 400mA$
Forward Recovery Time	$t_{fr}$		10	ns	$I_F = 10mA$
Diode Capacitance	$C_d$		4	pF	$V_R = 1V, f = 1MHz$
Forward Overshoot Voltage	$V_{fr}$		Typ 0.9	V	$I_F = 10mA$ , Rise time = $5ns \pm 20\%$
Forward Voltage	$V_F$		1.4	V	$I_F = -200mA$

\*Time for  $I_R$  to recover to 10% of  $I_R$  peak  
For typical characteristics graphs see FLLD263 datasheet.